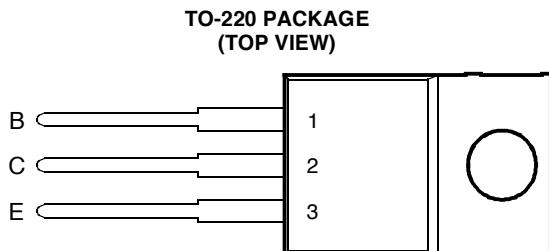


- Rugged Triple-Diffused Planar Construction
- 2.5 A Continuous Collector Current
- Operating Characteristics Fully Guaranteed at 100°C
- 850 Volt Blocking Capability
- 50 W at 25°C Case Temperature



This series is obsolete and not recommended for new designs.



Pin 2 is in electrical contact with the mounting base.

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#### absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT
Collector-base voltage ( $I_E = 0$ )	$V_{CBO}$	850	V
Collector-emitter voltage ( $V_{BE} = 0$ )	$V_{CES}$	850	V
Collector-emitter voltage ( $I_B = 0$ )	$V_{CEO}$	400	V
Emitter-base voltage	$V_{EBO}$	10	V
Continuous collector current	$I_C$	2.5	A
Peak collector current (see Note 1)	$I_{CM}$	8	A
Continuous device dissipation at (or below) 25°C case temperature	$P_{tot}$	50	W
Operating junction temperature range	$T_j$	-65 to +150	°C
Storage temperature range	$T_{stg}$	-65 to +150	°C

NOTE 1: This value applies for  $t_p \leq 10$  ms, duty cycle  $\leq 2\%$ .

#### PRODUCT INFORMATION

**electrical characteristics at 25°C case temperature (unless otherwise noted)**

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT	
$V_{CEO(sus)}$	Collector-emitter sustaining voltage	$I_C = 100 \text{ mA}$	$L = 25 \text{ mH}$	(see Note 2)	400			V
$I_{CES}$	Collector-emitter cut-off current	$V_{CE} = 850 \text{ V}$	$V_{BE} = 0$			5		$\mu\text{A}$
$I_{CEO}$	Collector cut-off current	$V_{CE} = 850 \text{ V}$	$V_{BE} = 0$	$T_C = 100^\circ\text{C}$		200		$\mu\text{A}$
$I_{EBO}$	Emitter cut-off current	$V_{EB} = 10 \text{ V}$	$I_C = 0$			5		$\mu\text{A}$
$I_{EBO}$	Emitter cut-off current	$V_{EB} = 10 \text{ V}$	$I_C = 0$			1		mA
$h_{FE}$	Forward current transfer ratio	$V_{CE} = 5 \text{ V}$	$I_C = 0.5 \text{ A}$	(see Notes 3 and 4)	20		60	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_B = 0.2 \text{ A}$	$I_C = 1 \text{ A}$	(see Notes 3 and 4)		1.0		V
		$I_B = 0.5 \text{ A}$	$I_C = 2.5 \text{ A}$			2.5		
		$I_B = 0.5 \text{ A}$	$I_C = 2.5 \text{ A}$	$T_C = 100^\circ\text{C}$		5.0		V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_B = 0.2 \text{ A}$	$I_C = 1 \text{ A}$	(see Notes 3 and 4)		1.0		V
		$I_B = 0.5 \text{ A}$	$I_C = 2.5 \text{ A}$			1.2		
		$I_B = 0.5 \text{ A}$	$I_C = 2.5 \text{ A}$	$T_C = 100^\circ\text{C}$		1.3		V
$f_t$	Current gain bandwidth product	$V_{CE} = 10 \text{ V}$	$I_C = 0.5 \text{ A}$	$f = 1 \text{ MHz}$		12		MHz
$C_{ob}$	Output capacitance	$V_{CB} = 20 \text{ V}$	$I_E = 0$	$f = 0.1 \text{ MHz}$	55			pF

NOTES: 2. Inductive loop switching measurement.

3. These parameters must be measured using pulse techniques,  $t_p = 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .

4. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

**thermal characteristics**

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			2.5	$^\circ\text{C/W}$

**inductive-load-switching characteristics at 25°C case temperature (unless otherwise noted)**

PARAMETER	TEST CONDITIONS <sup>†</sup>			MIN	TYP	MAX	UNIT
$t_{sv}$	Voltage storage time					2	$\mu\text{s}$
$t_{rv}$	Voltage rise time					200	ns
$t_{fi}$	Current fall time	$I_C = 2.5 \text{ A}$	$I_{B(on)} = 0.5 \text{ A}$	(see Figures 1 and 2)		200	ns
$t_{ti}$	Current tail time	$V_{BE(off)} = -5 \text{ V}$				50	ns
$t_{xo}$	Cross over time					300	ns
$t_{sv}$	Voltage storage time					2.5	$\mu\text{s}$
$t_{rv}$	Voltage rise time	$I_C = 2.5 \text{ A}$	$I_{B(on)} = 0.5 \text{ A}$	(see Figures 1 and 2)		400	ns
$t_{fi}$	Current fall time	$V_{BE(off)} = -5 \text{ V}$				250	ns
$t_{ti}$	Current tail time					50	ns
$t_{xo}$	Cross over time	$T_C = 100^\circ\text{C}$				500	ns

<sup>†</sup> Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

**PRODUCT INFORMATION**

MARCH 1984 - REVISED SEPTEMBER 2002  
Specifications are subject to change without notice.

## PARAMETER MEASUREMENT INFORMATION

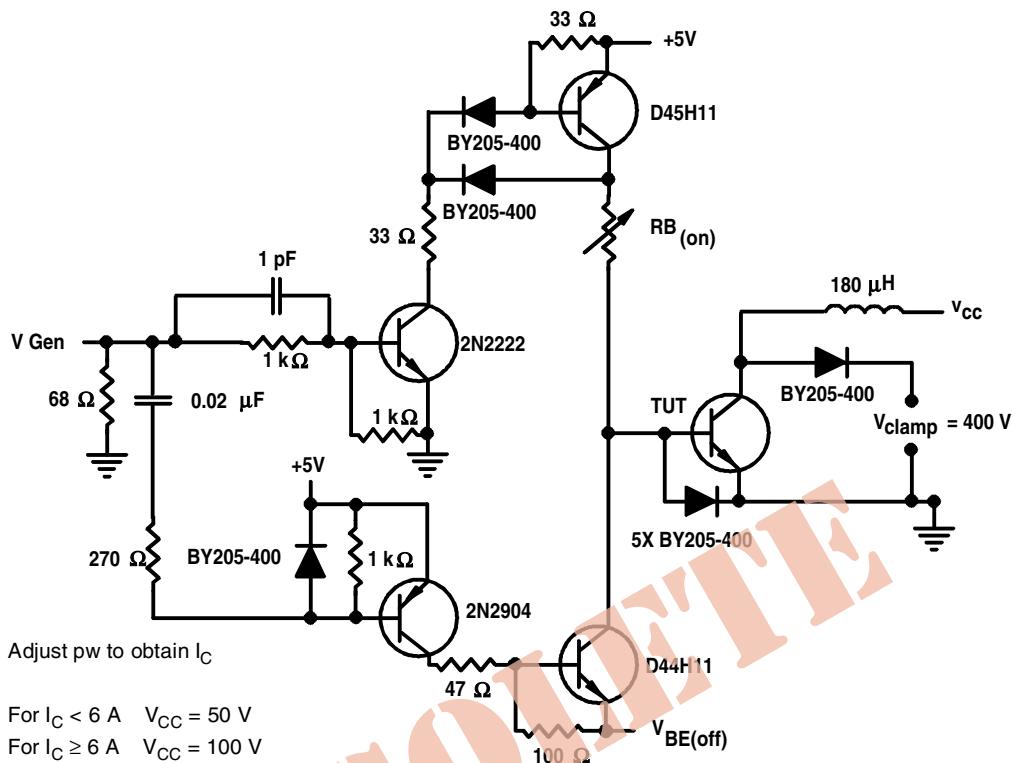
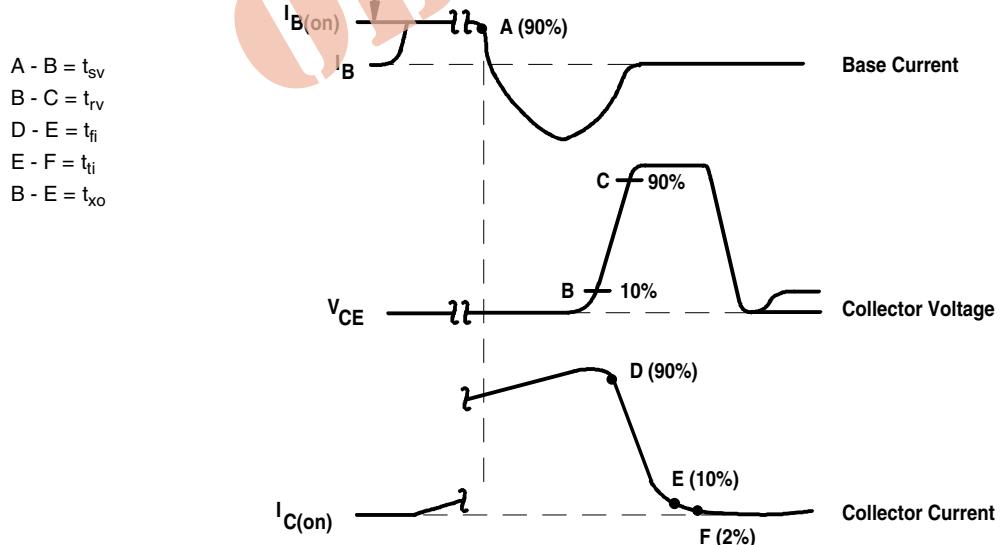


Figure 1. Inductive-Load Switching Test Circuit



NOTES: A. Waveforms are monitored on an oscilloscope with the following characteristics:  $t_r < 15$  ns,  $R_{in} > 10 \Omega$ ,  $C_{in} < 11.5$  pF.  
 B. Resistors must be noninductive types.

Figure 2. Inductive-Load Switching Waveforms

**PRODUCT INFORMATION**

### TYPICAL CHARACTERISTICS

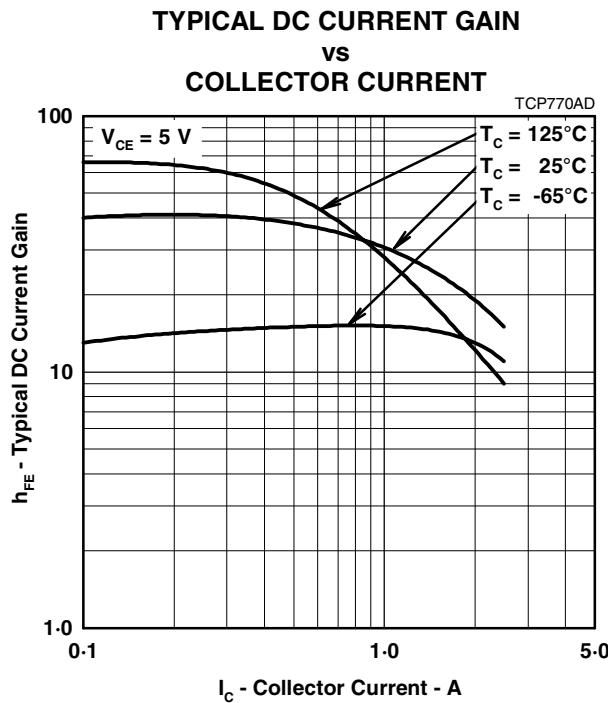


Figure 3.

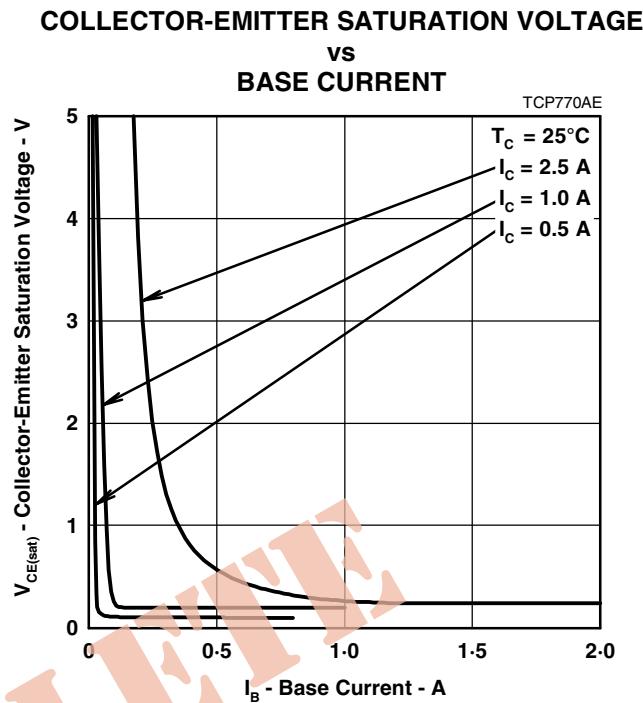


Figure 4.

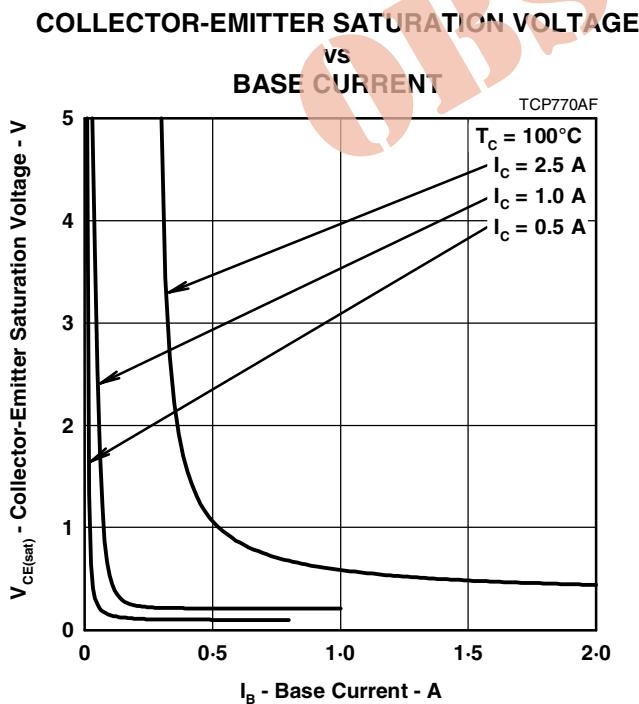


Figure 5.

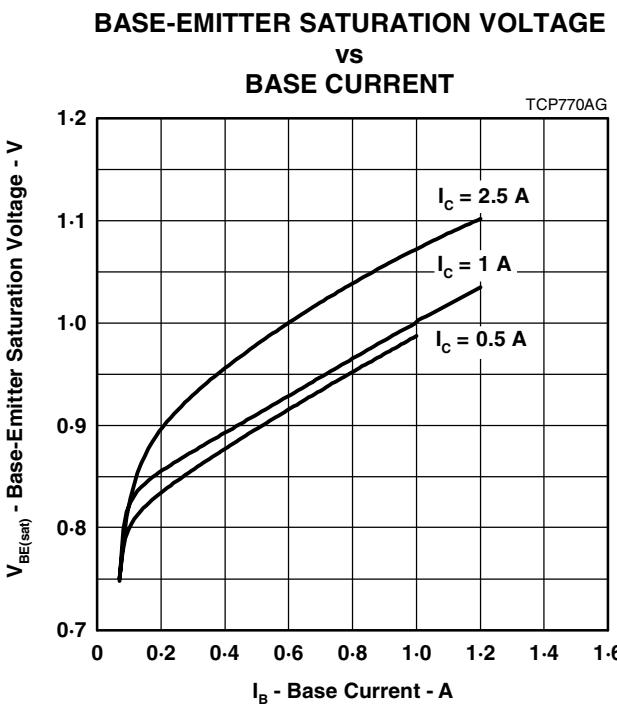


Figure 6.

### PRODUCT INFORMATION

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## MAXIMUM SAFE OPERATING REGIONS

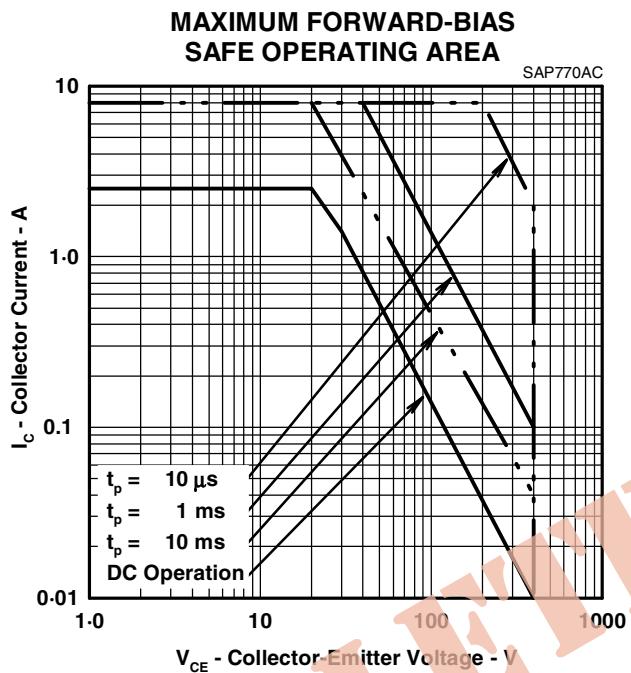


Figure 7.

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